Regarding the change of names mentioned in the document, such as Hitachi Electric and Hitachi XX, to Renesas Technology Corp.

The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp. Customer Support Dept. April 1, 2003



Cautions

Keep safety first in your circuit designs!

 Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- 1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corporation product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corporation or a third party.
- 2. Renesas Technology Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
- 3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor for the latest product information before purchasing a product listed herein.

The information described here may contain technical inaccuracies or typographical errors. Renesas Technology Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.

Please also pay attention to information published by Renesas Technology Corporation by various means, including the Renesas Technology Corporation Semiconductor home page (http://www.renesas.com).

- 4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
- 5. Renesas Technology Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- 6. The prior written approval of Renesas Technology Corporation is necessary to reprint or reproduce in whole or in part these materials.
- 7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.

Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.

8. Please contact Renesas Technology Corporation for further details on these materials or the products contained therein.

Octal Buffers / Drivers with 3-state Outputs

RENESAS

ADE-205-272A (Z)

2nd. Edition Jul. 2001

Description

The HD74V240A has eight inverter drivers with three-state outputs in a 20-pin package. Four inverters are included in one circuit. Each circuit can be independently controlled by the enable signal $1\overline{OE}$ or $2\overline{OE}$, which enables outputs when receiving a low-level signal. Low-voltage operation is suitable for battery-powered products (e.g., notebook computers), and the low-power consumption extends the battery life.

Features

- $V_{cc} = 2.0 \text{ V}$ to 5.5 V operation
- All inputs V_{IH} (Max.) = 5.5 V (@V_{cc} = 0 V to 5.5 V)
- All outputs V_0 (Max.) = 5.5 V (@V_{cc} = 0 V)
- Typical V_{oL} ground bounce < 0.8 V (@V_{cc} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.3 V (@V_{CC} = 3.3 V, Ta = 25°C)
- Output current $\pm 8 \text{ mA}$ (@V_{cc} = 3.0 V to 3.6 V), $\pm 16 \text{ mA}$ (@V_{cc} = 4.5 V to 5.5 V)

Function Table

In	nuts
	puis

ŌĒ	А	Output Y
L	Н	L
L	L	н
Н	X	Z

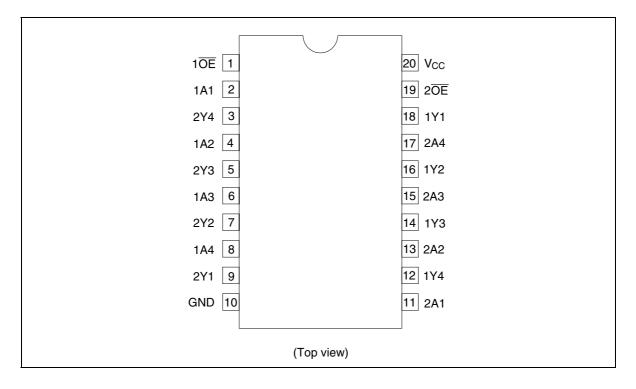
Note: H: High level

L: Low level

X: Immaterial

Z: High impedance

Pin Arrangement





Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range*1	V	-0.5 to 7.0	V	
Output voltage range*1,2	V _o	–0.5 to V $_{\rm cc}$ + 0.5	V	Output: H or L
		-0.5 to 7.0	-	V _{cc} : OFF or Output: Z
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	I _{ок}	±50	mA	V_{o} < 0 or V_{o} > V_{cc}
Continuous output current	I _o	±35	mA	$V_{o} = 0$ to V_{cc}
Continuous current through V_{cc} or GND	$I_{\rm cc}$ or $I_{\rm gnd}$	±70	mA	
Maximum power dissipation at Ta = 25° C (in still air)* ³	P _T	835	mW	SOP
		757	-	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded even if the input and output clampcurrent ratings are observed.

2. This value is limited to 5.5 V maximum.

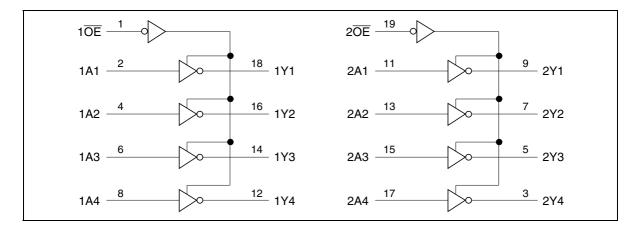
3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Item	Symbol	Min	Мах	Unit	Conditions
Supply voltage range	V _{cc}	2.0	5.5	V	
Input voltage range	V	0	5.5	V	
Output voltage range	Vo	0	V _{cc}	V	H or L
		0	5.5		High impedance state
Output current	I _{он}	_	-50	μA	$V_{cc} = 2.0 V$
		_	-2	mA	$V_{\rm cc}$ = 2.3 to 2.7 V
		_	-8		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	-12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
	I _{ol}	_	50	μA	$V_{cc} = 2.0 V$
		_	2	mA	$V_{\rm cc}$ = 2.3 to 2.7 V
		_	8		$V_{cc} = 3.0 \text{ to } 3.6 \text{ V}$
		_	12		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Input transition rise or fall rate	$\Delta t / \Delta v$	0	200	ns/V	V_{cc} = 2.3 to 2.7 V
		0	100		V_{cc} = 3.0 to 3.6 V
		0	20		$V_{cc} = 4.5 \text{ to } 5.5 \text{ V}$
Operating free-air temperature	Та	-40	85	°C	

Recommended Operating Conditions

Note: Unused or floating inputs must be held high or low.

Logic Diagram



DC Electrical Characteristics

Ta = -40 to $85^{\circ}C$

Item	Symbol	V _{cc} (V)*	Min	Тур	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.0	1.5	_	—	V	
		2.3 to 2.7	$V_{cc} imes 0.7$	_	_	-	
		3.0 to 3.6	$V_{cc} imes 0.7$	—		-	
		4.5 to 5.5	$V_{cc} imes 0.7$	_	_	-	
	V _L	2.0	_	_	0.5		
		2.3 to 2.7	_	_	$V_{cc} imes 0.3$		
		3.0 to 3.6	_	_	$V_{cc} imes 0.3$		
		4.5 to 5.5	_	_	$V_{cc} imes 0.3$		
Output voltage	V _{oh}	Min to Max	$V_{cc} - 0.1$	_	_	V	I _{oH} = -50 μA
		2.3	2.0	_	—	-	$I_{OH} = -2 \text{ mA}$
		3.0	2.48	_	_		I _{он} = —8 mA
		4.5	3.8	_	—		I _{он} = -16 mA
	V _{oL}	Min to Max	—	—	0.1	-	I _{oL} = 50 μA
		2.3	_	_	0.4	-	$I_{oL} = 2 \text{ mA}$
		3.0	_	_	0.44	-	$I_{oL} = 8 \text{ mA}$
		4.5	_	_	0.55		I _{oL} = 16 mA
Input current	I _{IN}	0 to 5.5	_	_	±1	μA	$V_{IN} = 5.5 \text{ V or GND}$
Off-state output current	I _{oz}	5.5	_	_	±5	μA	$V_{o} = V_{cc}$ or GND
Quiescent supply current	I _{cc}	5.5	—	—	20	μA	$V_{IN} = V_{CC}$ or GND, $I_{O} = 0$
Output leakage current		0	_	—	5	μA	$V_{_{\rm I}}$ or $V_{_{\rm O}}$ = 0 V to 5.5 V
Input capacitance	C _{IN}	3.3	_	2.3	_	pF	$V_1 = V_{cc}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

		Ta =	25°C		Ta = -40 to 85°C					
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	—	6.3	11.6	1.0	14.0	ns	$C_{L} = 15 \text{ pF}$	A	Y
		_	8.2	14.4	1.0	17.0	_	C _L = 50 pF		
Enable time	t _{zH} t _{zL}	_	8.5	14.6	1.0	17.0	ns	$C_{L} = 15 \text{ pF}$	ŌĒ	Y
		_	10.3	17.8	1.0	21.0	-	C _L = 50 pF		
Disable time	t _{HZ} t _{LZ}	_	9.7	14.1	1.0	16.0	ns	$C_{L} = 15 \text{ pF}$	ŌĒ	Y
			14.2	19.2	1.0	21.0	-	C _L = 50 pF		

 $V_{cc} = 3.3 \pm 0.3 \text{ V}$

 $V_{cc} = 2.5 \pm 0.2 \text{ V}$

		Ta =	25°C		Ta = -40 to 85°C					
Item	Symbol Min Typ Max Min Max		Max	Unit	Test Conditions	FROM (Input)	TO (Output)			
Propagation delay time	t _{PLH} t _{PHL}	_	4.6	7.5	1.0	9.0	ns	C _L = 15 pF	A	Υ
		_	5.9	11.0	1.0	12.5	_	C _L = 50 pF		
Enable time	t _{zH} t _{zL}	_	6.2	10.6	1.0	12.5	ns	$C_{L} = 15 \text{ pF}$	ŌĒ	Y
		_	7.5	14.1	1.0	16.0	-	C _L = 50 pF		
Disable time	t _{HZ} t _{LZ}	_	8.3	12.5	1.0	13.5	ns	$C_{L} = 15 \text{ pF}$	ŌĒ	Y
		_	11.8	15.0	1.0	17.0	_	$C_{L} = 50 \text{ pF}$		

Switching Characteristics (cont)

			~		
V _{cc}	_	5 ()+	05	i V
• CC	_	2.0	<u>ب</u>	0.2	· •

		Ta =	25°C		Ta = −40 to 85°C					
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Test Conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{plH} t _{pHL}	_	3.4	5.5	1.0	6.5	ns	C _L = 15 pF	A	Υ
		_	4.4	7.5	1.0	8.5	-	C _L = 50 pF	—	
Enable time	t _{zн} t _{zl}	_	4.6	7.3	1.0	8.5	ns	C _L = 15 pF	ŌĒ	Y
			5.6	9.3	1.0	10.5	-	C _L = 50 pF	_	
Disable time	t _{HZ} t _{LZ}	_	7.4	12.2	1.0	13.5	ns	C _L = 15 pF	ŌĒ	Y
		_	9.7	14.2	1.0	15.5	-	C _∟ = 50 pF		

Output-skew Characteristics

 $C_{L} = 50 \text{ pF}$

			Ta = 25°C		Ta = -40 to	85°C	
ltem	Symbol	V_{cc} (V)	Min	Max	Min	Max	Unit
Output skew	t _{sk (O)}	2.3 to 2.7	_	2.0	_	2.0	ns
		3.0 to 3.6	_	1.5	_	1.5	-
		4.5 to 5.5	_	1.0	_	1.0	_

Note: Skew between any outputs of the same package switching in the same direction. This parameter is warranted but not production tested.

Operating Characteristics

 $C_{L} = 50 \text{ pF}$

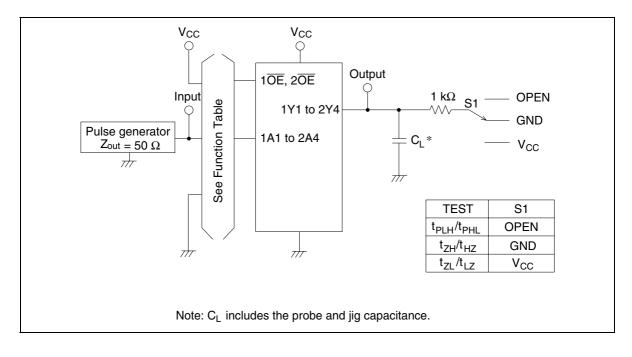
			Ta = 25	0°C			
Item	Symbol	V_{cc} (V)	Min	Тур	Мах	Unit	Test Conditions
Power dissipation capacitance	$C_{_{PD}}$	3.3	_	14.0	_	pF	f = 10 MHz
		5.0		16.4			

Noise Characteristics

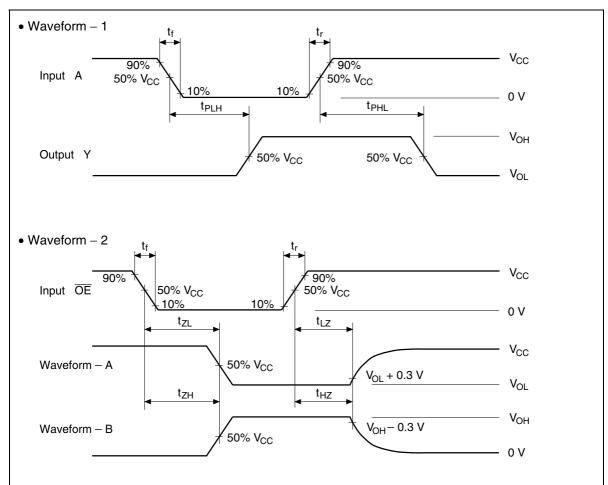
 $C_{L} = 50 \text{ pF}$

			Ta = 25°C				
Item	Symbol	V_{cc} (V)	Min	Тур	Max	Unit	Test Conditions
Quiet output, maximum dynamic V _{oL}	$V_{_{OL(P)}}$	3.3	_	0.6	0.8	V	
Quiet output, minimum dynamic V _{oL}	$V_{OL(V)}$	3.3	_	-0.5	-0.8		
Quiet output, minimum dynamic V _{он}	$V_{OH(V)}$	3.3	_	2.8	_		
High-level dynamic input voltage	$V_{\text{IH (D)}}$	3.3	2.31	_	_	V	
Low-level dynamic inout voltage	$V_{\text{IL (D)}}$	3.3	_	_	0.99		

Test Circuit

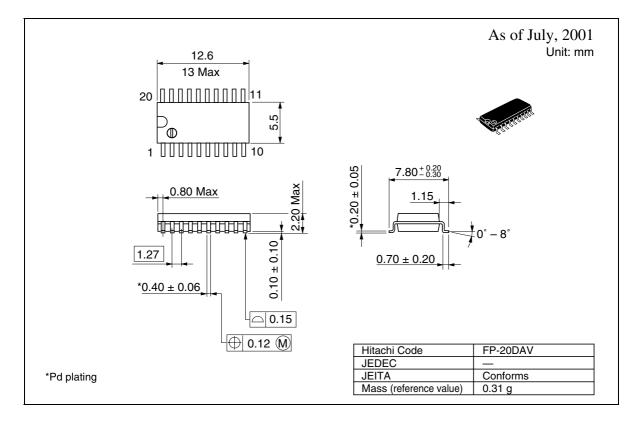


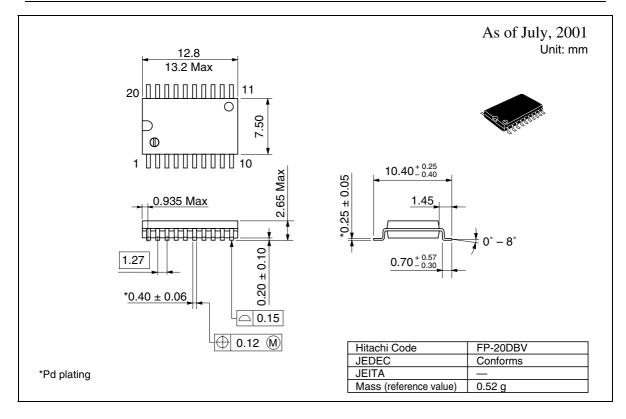


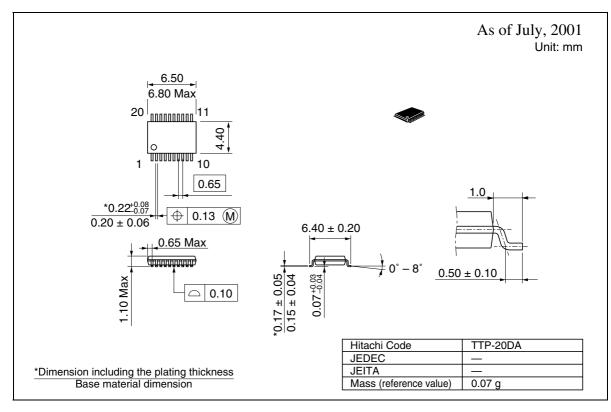


- Notes: 1. Input waveform: PRR \leq 1 MHz, Zo = 50 $\Omega,\,t_r \leq$ 3 ns, $t_f \leq$ 3 ns
 - 2. Waveform–A is for an output with internal conditions such that the output is low except when disabled by the output control.
 - 3. Waveform–B is for an output with internal conditions such that the output is high except when disabled by the output control.
 - 4. The output are measured one at a time with one transition per measurement.

Package Dimensions







Disclaimer

- Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, 1. copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
- 2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
- 3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as in aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
- 4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safe devices, so that the equipment incorporating the Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
- This product is not designed to be radiation resistant. 5.
- 6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
- 7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

Sales Offices



Hitachi. Ltd.

Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia	: http://sicapac.hitachi-asia.com
	Japan	: http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to: chi Europe GmbH

Hitachi Semiconductor	Hitachi Europe GmbH
(America) Inc.	Electronic Components Group
179 East Tasman Drive,	Dornacher Stra§e 3
San Jose,CA 95134	D-85622 Feldkirchen, Munich
Tel: <1> (408) 433-1990	Germany
Fax: <1>(408) 433-0223	Tel: <49> (89) 9 9180-0
	Fax: <49> (89) 9 29 30 00

622 Feldkirchen, Munich nany <49> (89) 9 9180-0 <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel : <886>-(2)-2718-3666 Tel: <44> (1628) 585000

Fax: <44> (1628) 585160

Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00, Singapore 049318 Tel: <65>-538-6533/538-8577 Fax : <65>-538-6933/538-3877 URL : http://www.hitachi.com.sg Hitachi Asia Ltd. (Taipei Branch Office)

4/F, No. 167, Tun Hwa North Road, Hung-Kuo Building, Taipei (105), Taiwan Fax : <886>-(2)-2718-8180 Telex : 23222 HAS-TP URL : http://www.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon, Hong Kong Tel : <852>-(2)-735-9218 Fax : <852>-(2)-730-0281 URL : http://www.hitachi.com.hk

Copyright © Hitachi, Ltd., 2001. All rights reserved. Printed in Japan. Colophon 2.0

